

SKR 20F



V_{RSM} V	V_{RRM} V	$I_{FRMS} = 30$ A (maximum value for continuous operation) $I_{FAV} = 20$ A (sin. 180; 50 Hz; $T_c = 85$ °C)	
1000	1000	SKR 20F10	
1200	1200	SKR 20F12	

Fast Recovery Rectifier Diode

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Features

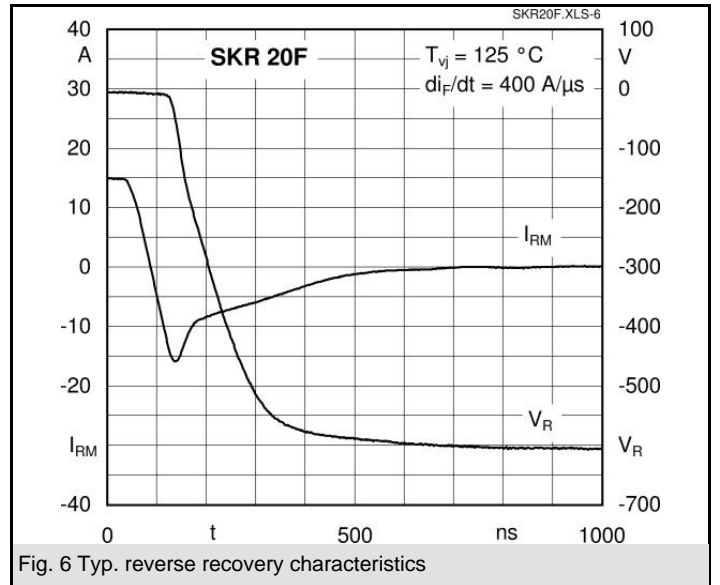
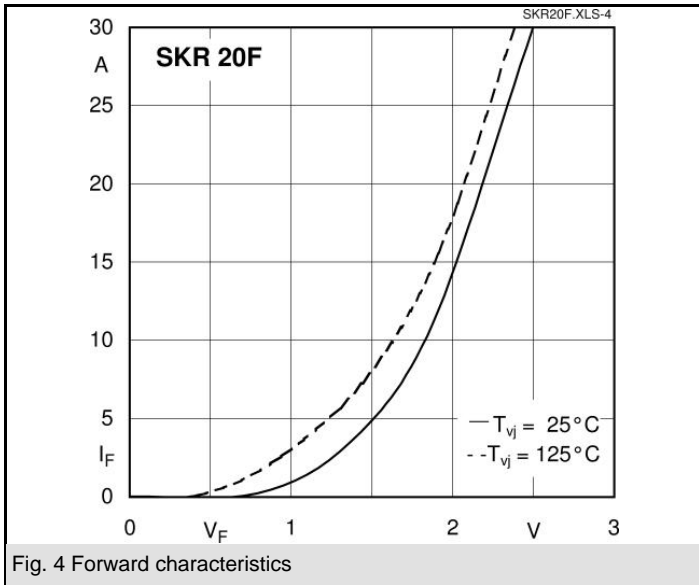
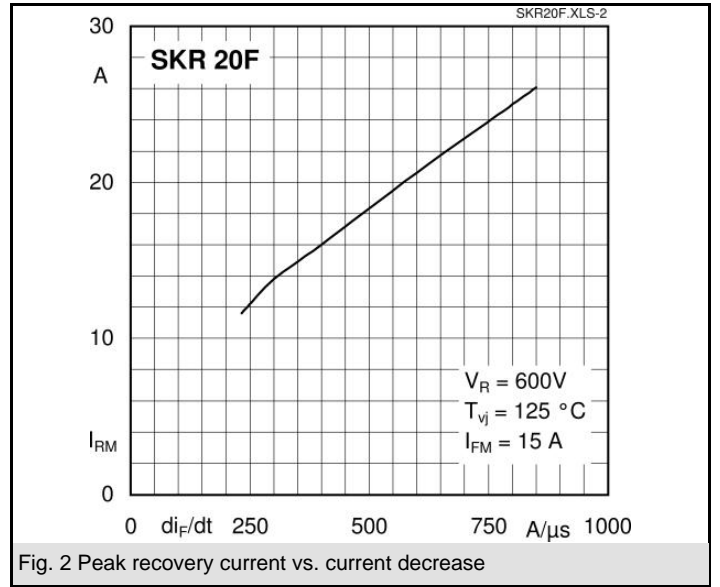
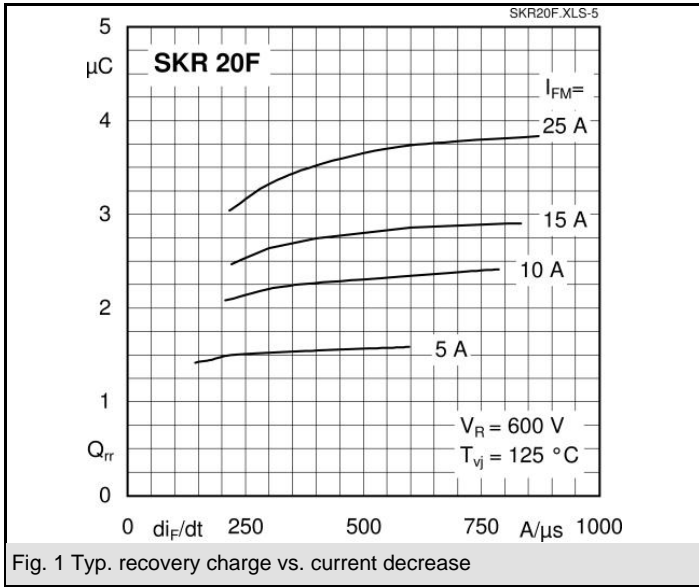
- CAL-Diode (controlled axial lifetime technology), patent no. DE 431044
- Very short recovery time
- Soft recovery under all conditions
- Up to 1200 V reverse voltage
- Epoxy meets UL 94V-0 flammability classification

Typical Applications

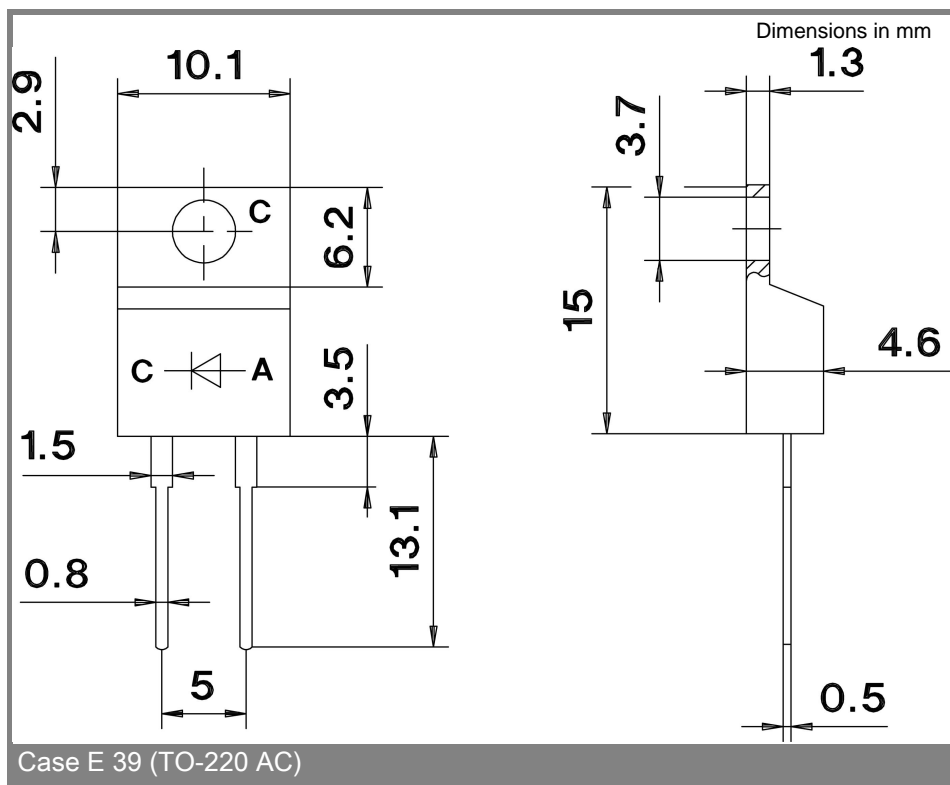
- Inverse diode for power transistors
- Inverter
- Power supply
- Snubber and clamping diode

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 85$ (100) °C	20 (17)	A
I_{FSM}	$T_{vj} = 25$ °C; 10 ms	150	A
i^2t	$T_{vj} = 150$ °C; 10 ms	140	A
	$T_{vj} = 25$ °C; 8,3 ... 10 ms	110	A ² s
V_F	$T_{vj} = 25$ °C; $I_F = 15$ A	max. 2,5	V
	$T_{vj} = 150$ °C	max. 1,2	V
$V_{(TO)}$	$T_{vj} = 150$ °C	max. 70	mΩ
r_T	$T_{vj} = 25$ °C; $V_{RD} = V_{RRM}$	max. 0,1	mA
I_{RD}	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}$	max. 2	mA
Q_{rr}	$T_{vj} = 125$ °C, $I_F = 15$ A, -di/dt = 400 A/μs, $V_R = 600$ V	2,7	μC
I_{RM}		16	A
t_{rr}		380	ns
E_{rr}		-	mJ
$R_{th(j-c)}$		0,7	K/W
$R_{th(c-s)}$		0,3	K/W
T_{vj}		- 40 ... 150	°C
T_{stg}		- 40 ... 150	°C
V_{isol}		-	V~
M_s	to heatsink	0,55 ... 0,8	Nm
a			m/s ²
m	approx.	2	g
Case		E 39	





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